



The products are Darlington transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

High isolation 3750 VRMS

Operating temperature range -55°C to 110°C

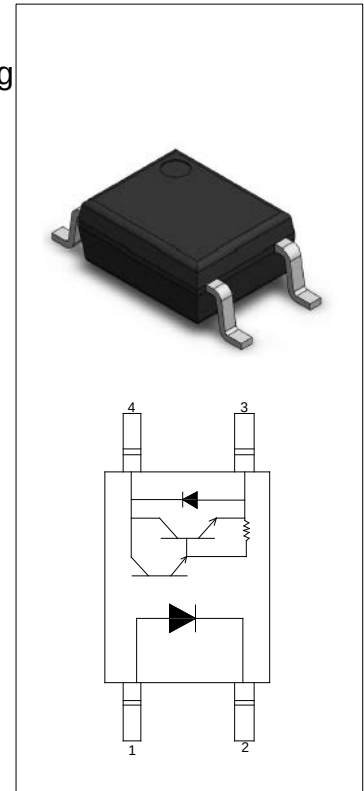
RoHS & REACH Compliance

HBM: H3A; MM: M4; CDM: C3

CQC approved

VDE approved

UL approved



(Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1 ^①	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	6	V
	Collector Current	I_C	150	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	225	mW
Isolation Voltage		V_{iso}	3750 ^②	Vrms
Operating Temperature		T_{opr}	-55~+110	°C
Junction Temperature		T_j	125	°C

Storage Temperature	T _{stg}	-55~+125	°C
Soldering Temperature	T _{sol}	260	°C

100μs pulse, 100Hz frequency

AC for 1minute, R.H.=40~60%

(Temperature=25°C)

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	V _F	I _F =10mA	-	1.2	1.5	V
	Reverse Current	I _R	V _R =6V	-	-	1	μA
	Terminal Capacitance	C _t	V=0, f=1MHz	-	10	-	pF
Output	Collector-Emitter dark current	I _{CEO}	V _{CE} =20V, I _F =0	-	-	200	nA
	Collector-Emitter breakdown voltage	BV _{CEO}	I _C =0.1mA I _F =0	80	-	-	V
	Emitter-Collector breakdown voltage	BV _{ECO}	I _E =0.1mA I _F =0	6	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	I _F =1mA V _{CE} =2V	1000	-	7500	%
	Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _F =1mA I _C =10mA	-	-	1	V
	Isolation resistance	R _{io}	DC500V 40~60%R.H.	10 ¹²	-	-	Ω
	Floating Capacitance	C _{io}	V=0, f=1MHz	-	0.8	-	pF
	Rise Time	t _r	V _{CE} =10V, I _C =10mA R _L =100Ω	-	40	-	μs
	Fall Time	t _f		-	15	-	μs
	Response Time	t _{on}		-	50	-	μs
		t _{off}		-	15	-	μs

Rank Table of Current Transfer Ratio (Temperature=25°C)

Grade Sign	Test Condition	Min. (%)	Max. (%)
	I _F ② CE	-	110
J	I _F =29 CE	450	-

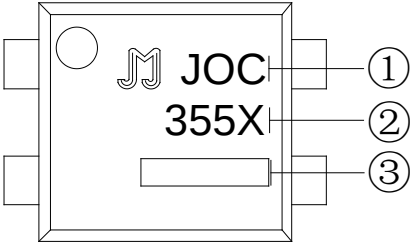


FIG.1: Max. Allowable LED Forward Current vs. Ambient Temperature

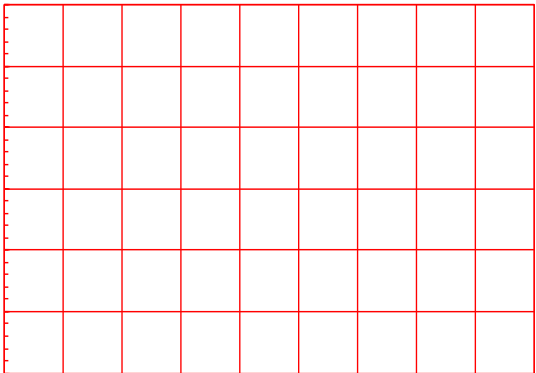
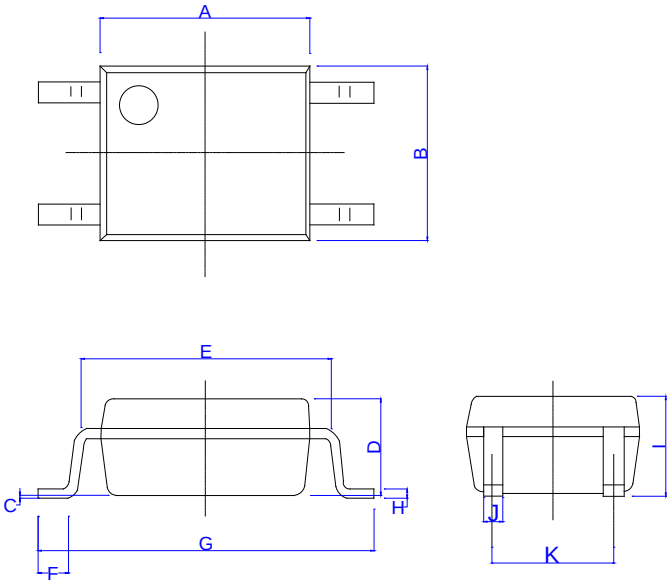
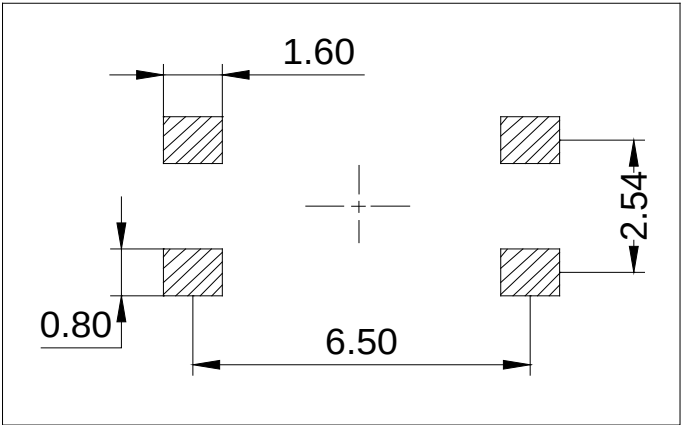


FIG.2: Collector Power Dissipation vs. Ambient Temperature (T_{amb})

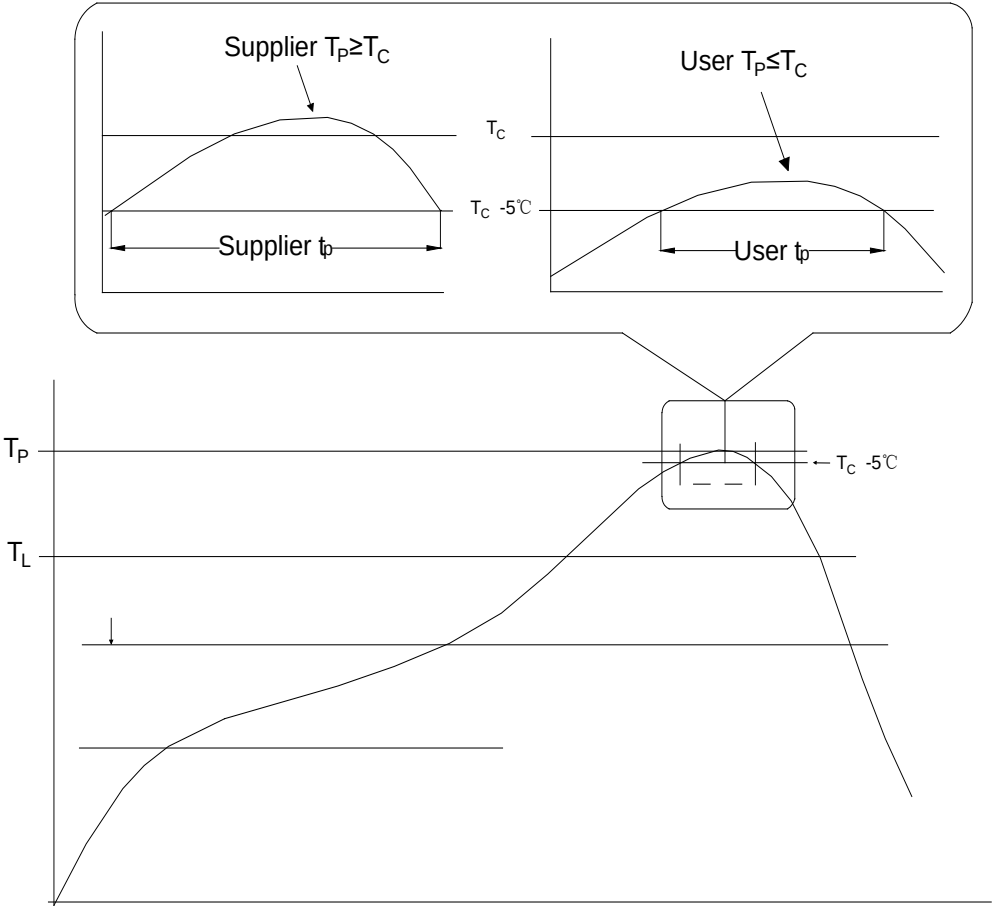


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	3.60		4.20	0.142		0.165
C	0.00		0.20	0.000		0.008
D	1.90		2.30	0.075		0.091
E	5.00		5.60	0.197		0.220
F	0.34		0.94	0.013		0.037
G	6.70		7.30	0.264		0.287
H	0.10		0.30	0.004		0.012
I	2.00		2.40	0.079		0.094
J	0.25		0.55	0.010		0.022
K	2.29		2.79	0.090		0.110



Option T1

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Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;
Recommend storage humidity: <60%;
MSL level: MSL 1

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